

Initially, diffusion current is large and drift current is small. As the diffusion process continues, the space-charge regions on either side of the junction extend, thus increasing the electric field strength and hence drift current. This process continues until the diffusion current equals the drift current. Thus a p-n junction is formed. In a p-n junction under equilibrium there is *no net current*.

The loss of electrons from the n-region and the gain of electron by the p-region causes a difference of potential across the junction of the two regions. The polarity of this potential is such as to oppose further flow of carriers so that a condition of equilibrium exists. Figure 14.11 shows the p-n junction at equilibrium and the potential across the junction. The n-material has lost electrons, and p material has acquired electrons. The n material is thus positive relative to the p material. Since this potential tends to prevent the movement of electron from the n region into the p region, it is often called a *barrier potential*.

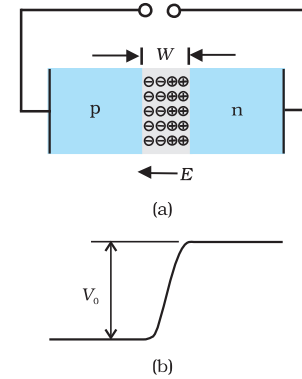


FIGURE 14.11 (a) Diode under equilibrium ($V = 0$), (b) Barrier potential under no bias.

Example 14.3 Can we take one slab of p-type semiconductor and physically join it to another n-type semiconductor to get p-n junction?

Solution No! Any slab, howsoever flat, will have roughness much larger than the inter-atomic crystal spacing (~2 to 3 Å) and hence *continuous contact* at the atomic level will not be possible. The junction will behave as a *discontinuity* for the flowing charge carriers.

EXAMPLE 14.3

14.6 SEMICONDUCTOR DIODE

A semiconductor diode [Fig. 14.12(a)] is basically a p-n junction with metallic contacts provided at the ends for the application of an external voltage. It is a two terminal device. A p-n junction diode is symbolically represented as shown in Fig. 14.12(b).

The direction of arrow indicates the conventional direction of current (when the diode is under forward bias). The equilibrium barrier potential can be altered by applying an external voltage V across the diode. The situation of p-n junction diode under equilibrium (without bias) is shown in Fig. 14.11(a) and (b).

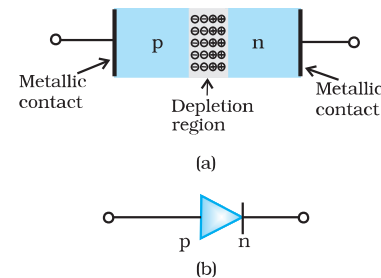


FIGURE 14.12 (a) Semiconductor diode, (b) Symbol for p-n junction diode.

14.6.1 p-n junction diode under forward bias

When an external voltage V is applied across a semiconductor diode such that p-side is connected to the positive terminal of the battery and n-side to the negative terminal [Fig. 14.13(a)], it is said to be *forward biased*.

The applied voltage mostly drops across the depletion region and the voltage drop across the p-side and n-side of the junction is negligible. (This is because the resistance of the depletion region – a region where there are no charges – is very high compared to the resistance of n-side and p-side.) The direction of the applied voltage (V) is opposite to the

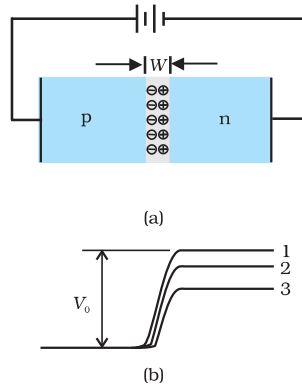


FIGURE 14.13 (a) p-n junction diode under forward bias, (b) Barrier potential (1) without battery, (2) Low battery voltage, and (3) High voltage battery.

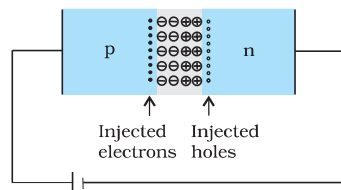


FIGURE 14.14 Forward bias minority carrier injection.

built-in potential V_0 . As a result, the depletion layer width decreases and the barrier height is reduced [Fig. 14.13(b)]. The effective barrier height under forward bias is $(V_0 - V)$.

If the applied voltage is small, the barrier potential will be reduced only slightly below the equilibrium value, and only a small number of carriers in the material—those that happen to be in the uppermost energy levels—will possess enough energy to cross the junction. So the current will be small. If we increase the applied voltage significantly, the barrier height will be reduced and more number of carriers will have the required energy. Thus the current increases.

Due to the applied voltage, electrons from n-side cross the depletion region and reach p-side (where they are minority carries). Similarly, holes from p-side cross the junction and reach the n-side (where they are minority carries). This process under forward bias is known as minority carrier injection. At the junction boundary, on each side, the minority carrier concentration increases significantly compared to the locations far from the junction.

Due to this concentration gradient, the injected electrons on p-side diffuse from the junction edge of p-side to the other end of p-side. Likewise, the injected holes on n-side diffuse from the junction edge of n-side to the other end of n-side (Fig. 14.14). This motion of charged carriers on either side gives rise to current. The total diode forward current is sum of hole diffusion current and conventional current due to electron diffusion. The magnitude of this current is usually in mA.

14.6.2 p-n junction diode under reverse bias

When an external voltage (V) is applied across the diode such that n-side is positive and p-side is negative, it is said to be *reverse biased* [Fig.14.15(a)]. The applied voltage mostly drops across the depletion region. The direction of applied voltage is same as the direction of barrier potential. As a result, the barrier height increases and the depletion region widens due to the change in the electric field. The effective barrier height under reverse bias is $(V_0 + V)$, [Fig. 14.15(b)]. This suppresses the flow of electrons from $n \rightarrow p$ and holes from $p \rightarrow n$. Thus, diffusion current, decreases enormously compared to the diode under forward bias.

The electric field direction of the junction is such that if electrons on p-side or holes on n-side in their random motion come close to the junction, they will be swept to its majority zone. This drift of carriers gives rise to current. The drift current is of the order of a few μA . This is quite low because it is due to the motion of carriers from their minority side to their majority side across the junction. The drift current is also there under forward bias but it is negligible (μA) when compared with current due to injected carriers which is usually in mA.

The diode reverse current is not very much dependent on the applied voltage. Even a small voltage is sufficient to sweep the minority carriers from one side of the junction to the other side of the junction. The current

is not limited by the magnitude of the applied voltage but is limited due to the concentration of the minority carrier on either side of the junction.

The current under reverse bias is essentially voltage independent upto a critical reverse bias voltage, known as breakdown voltage (V_{br}). When $V = V_{br}$, the diode reverse current increases sharply. Even a slight increase in the bias voltage causes large change in the current. If the reverse current is not limited by an external circuit below the rated value (specified by the manufacturer) the p-n junction will get destroyed. Once it exceeds the rated value, the diode gets destroyed due to overheating. This can happen even for the diode under forward bias, if the forward current exceeds the rated value.

The circuit arrangement for studying the V - I characteristics of a diode, (i.e., the variation of current as a function of applied voltage) are shown in Fig. 14.16(a) and (b). The battery is connected to the diode through a potentiometer (or rheostat) so that the applied voltage to the diode can be changed. For different values of voltages, the value of the current is noted. A graph between V and I is obtained as in Fig. 14.16(c). Note that in forward bias measurement, we use a milliammeter since the expected current is large (as explained in the earlier section) while a micrometer is used in reverse bias to measure the current. You can see in Fig. 14.16(c) that in forward

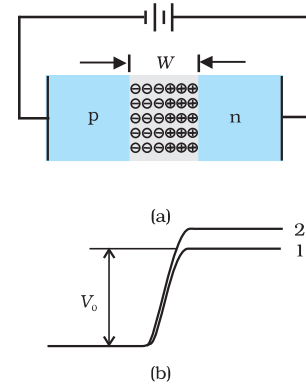


FIGURE 14.15 (a) Diode under reverse bias, (b) Barrier potential under reverse bias.

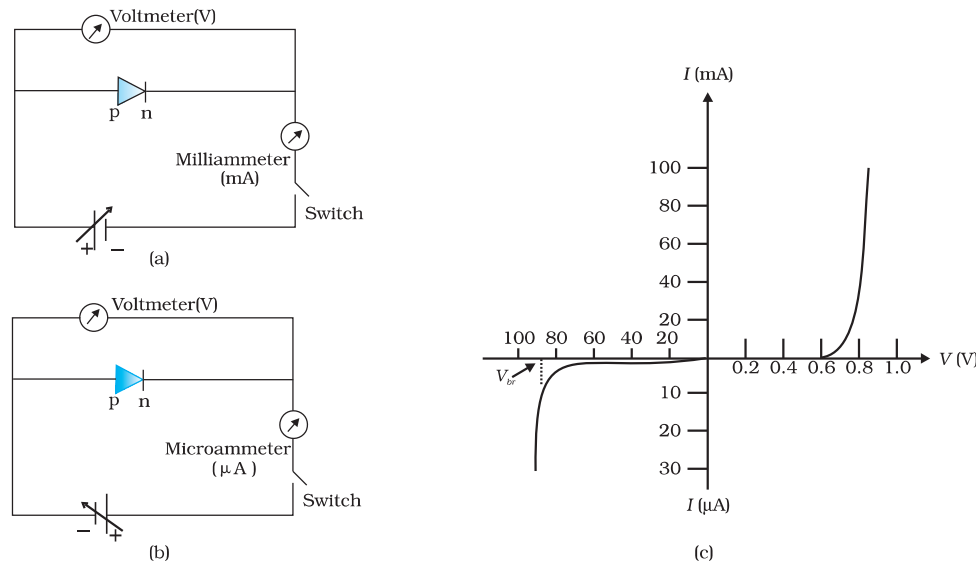


FIGURE 14.16 Experimental circuit arrangement for studying V - I characteristics of a p-n junction diode (a) in forward bias, (b) in reverse bias. (c) Typical V - I characteristics of a silicon diode.

bias, the current first increases very slowly, almost negligibly, till the voltage across the diode crosses a certain value. After the characteristic voltage, the diode current increases significantly (exponentially), even for a very small increase in the diode bias voltage. This voltage is called the *threshold voltage* or cut-in voltage ($\sim 0.2\text{V}$ for germanium diode and $\sim 0.7\text{V}$ for silicon diode).

For the diode in reverse bias, the current is very small ($\sim \mu\text{A}$) and almost remains constant with change in bias. It is called *reverse saturation current*. However, for special cases, at very high reverse bias (break down voltage), the current suddenly increases. This special action of the diode is discussed later in Section 14.8. The general purpose diode are not used beyond the reverse saturation current region.

The above discussion shows that the p-n junction diode primarily allows the flow of current only in one direction (forward bias). The forward bias resistance is low as compared to the reverse bias resistance. This property is used for rectification of ac voltages as discussed in the next section. For diodes, we define a quantity called *dynamic resistance* as the ratio of small change in voltage ΔV to a small change in current ΔI :

$$r_d = \frac{\Delta V}{\Delta I} \tag{14.6}$$

Example 14.4 The V - I characteristic of a silicon diode is shown in the Fig. 14.17. Calculate the resistance of the diode at (a) $I_D = 15\text{ mA}$ and (b) $V_D = -10\text{ V}$.

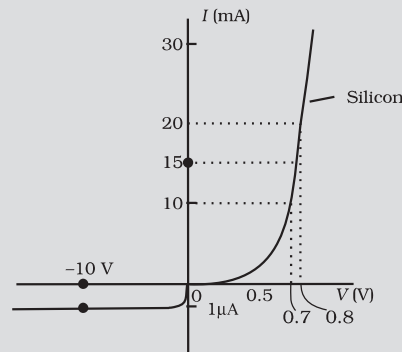


FIGURE 14.17

Solution Considering the diode characteristics as a straight line between $I = 10\text{ mA}$ to $I = 20\text{ mA}$ passing through the origin, we can calculate the resistance using Ohm's law.

(a) From the curve, at $I = 20\text{ mA}$, $V = 0.8\text{ V}$; $I = 10\text{ mA}$, $V = 0.7\text{ V}$

$$r_{fb} = \Delta V / \Delta I = 0.1\text{V} / 10\text{ mA} = 10\ \Omega$$

(b) From the curve at $V = -10\text{ V}$, $I = -1\ \mu\text{A}$,

Therefore,

$$r_{rb} = 10\text{ V} / 1\ \mu\text{A} = 1.0 \times 10^7\ \Omega$$

EXAMPLE 14.4

14.7 APPLICATION OF JUNCTION DIODE AS A RECTIFIER

From the V - I characteristic of a junction diode we see that it allows current to pass only when it is forward biased. So if an alternating voltage is applied across a diode the current flows only in that part of the cycle when the diode is forward biased. This property is used to *rectify* alternating voltages and the circuit used for this purpose is called a *rectifier*.

If an alternating voltage is applied across a diode in series with a load, a pulsating voltage will appear across the load only during the half cycles of the ac input during which the diode is forward biased. Such rectifier circuit, as shown in Fig. 14.18, is called a *half-wave rectifier*. The secondary of a transformer supplies the desired ac voltage across terminals A and B. When the voltage at A is positive, the diode is forward biased and it conducts. When A is negative, the diode is reverse-biased and it does not conduct. The reverse saturation current of a diode is negligible and can be considered equal to zero for practical purposes. (The reverse breakdown voltage of the diode must be sufficiently higher than the peak ac voltage at the secondary of the transformer to protect the diode from reverse breakdown.)

Therefore, in the positive *half-cycle* of ac there is a current through the load resistor R_L and we get an output voltage, as shown in Fig. 14.18(b), whereas there is no current in the negative half-cycle. In the next positive half-cycle, again we get the output voltage. Thus, the output voltage, though still varying, is restricted to *only one direction* and is said to be *rectified*. Since the rectified output of this circuit is only for half of the input ac wave it is called as *half-wave rectifier*.

The circuit using two diodes, shown in Fig. 14.19(a), gives output rectified voltage corresponding to both the positive as well as negative half of the ac cycle. Hence, it is known as *full-wave rectifier*. Here the p-side of the two diodes are connected to the ends of the secondary of the transformer. The n-side of the diodes are connected together and the output is taken between this common point of diodes and the midpoint of the secondary of the transformer. So for a full-wave rectifier the secondary of the transformer is provided with a centre tapping and so it is called *centre-tap transformer*. As can be seen from Fig.14.19(c) the voltage rectified by each diode is only half the total secondary voltage. Each diode rectifies only for half the cycle, but the two do so for alternate cycles. Thus, the output between their common terminals and the centre-tap of the transformer becomes a full-wave rectifier output. (Note that there is another circuit of full wave rectifier which does not need a centre-tap transformer but needs four diodes.) Suppose the input voltage to A

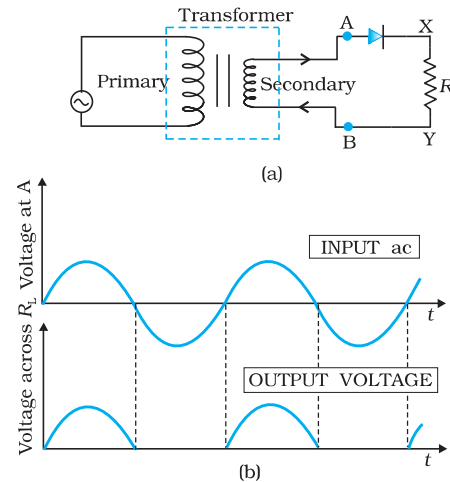


FIGURE 14.18 (a) Half-wave rectifier circuit, (b) Input ac voltage and output voltage waveforms from the rectifier circuit.

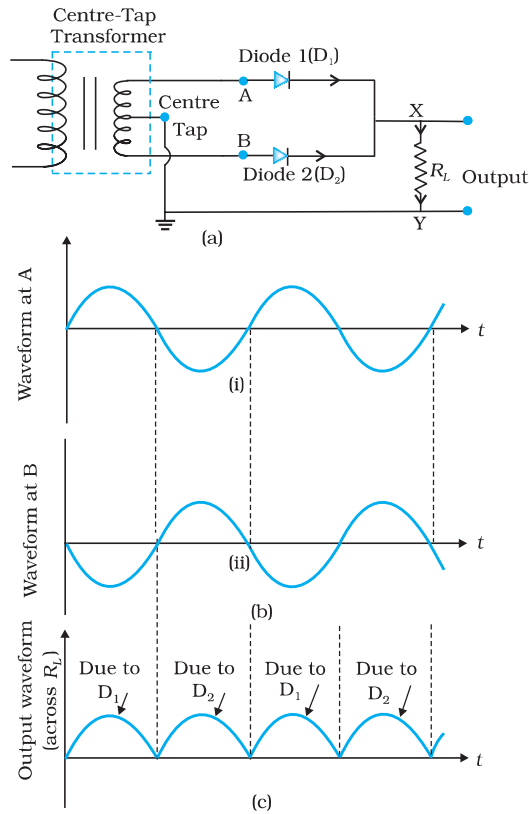


FIGURE 14.19 (a) A Full-wave rectifier circuit; (b) Input wave forms given to the diode D_1 at A and to the diode D_2 at B; (c) Output waveform across the load R_L connected in the full-wave rectifier circuit.

with respect to the centre tap at any instant is positive. It is clear that, at that instant, voltage at B being out of phase will be negative as shown in Fig. 14.19(b). So, diode D_1 gets forward biased and conducts (while D_2 being reverse biased is not conducting). Hence, during this positive half cycle we get an output current (and a output voltage across the load resistor R_L) as shown in Fig. 14.19(c). In the course of the ac cycle when the voltage at A becomes negative with respect to centre tap, the voltage at B would be positive. In this part of the cycle diode D_1 would not conduct but diode D_2 would, giving an output current and output voltage (across R_L) during the negative half cycle of the input ac. Thus, we get output voltage during both the positive as well as the negative half of the cycle. Obviously, this is a more efficient circuit for getting rectified voltage or current than the half-wave rectifier.

The rectified voltage is in the form of pulses of the shape of half sinusoids. Though it is unidirectional it does not have a steady value. To get steady dc output from the pulsating voltage normally a capacitor is connected across the output terminals (parallel to the load R_L). One can also use an inductor in series with R_L for the same purpose. Since these additional circuits appear to *filter* out the *ac ripple* and give a *pure dc* voltage, so they are called filters.

Now we shall discuss the role of capacitor in filtering. When the voltage across the capacitor is rising, it gets charged. If there is no external load, it remains charged to the peak voltage of the rectified output. When there is a load, it gets discharged through the load and the voltage across it begins to fall. In the next half-cycle of rectified output it again gets charged to the peak value (Fig. 14.20). The rate of fall of the voltage across the capacitor depends inversely upon the product of capacitance C and the effective resistance R_L used in the circuit and is called the *time constant*. To make the time constant large value of C should be large. So capacitor input filters use large capacitors. The *output voltage* obtained by using capacitor input filter is nearer to the *peak voltage* of the rectified voltage. This type of filter is most widely used in power supplies.

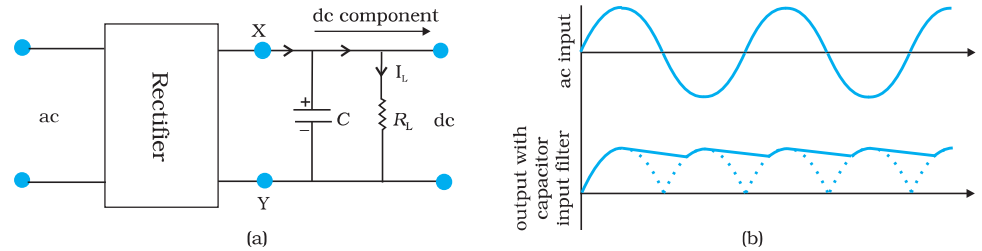


FIGURE 14.20 (a) A full-wave rectifier with capacitor filter, (b) Input and output voltage of rectifier in (a).

14.8 SPECIAL PURPOSE p-n JUNCTION DIODES

In this section, we shall discuss some devices which are basically junction diodes but are developed for different applications.

14.8.1 Zener diode

It is a special purpose semiconductor diode, named after its inventor C. Zener. It is designed to operate under reverse bias in the breakdown region and used as a voltage regulator. The symbol for Zener diode is shown in Fig. 14.21(a).

Zener diode is fabricated by heavily doping both p- and n- sides of the junction. Due to this, depletion region formed is very thin ($<10^{-6}$ m) and the electric field of the junction is extremely high ($\sim 5 \times 10^6$ V/m) even for a small reverse bias voltage of about 5V. The I-V characteristics of a Zener diode is shown in Fig. 14.21(b). It is seen that when the applied reverse bias voltage (V) reaches the breakdown voltage (V_z) of the Zener diode, there is a large change in the current. Note that after the breakdown voltage V_z , a large change in the current can be produced by almost insignificant change in the reverse bias voltage. In other words, Zener voltage remains constant, even though current through the Zener diode varies over a wide range. This property of the Zener diode is used for regulating supply voltages so that they are constant.

Let us understand how reverse current suddenly increases at the breakdown voltage. We know that reverse current is due to the flow of electrons (minority carriers) from p \rightarrow n and holes from n \rightarrow p. As the reverse bias voltage is increased, the electric field at the junction becomes significant. When the reverse bias voltage $V = V_z$, then the electric field strength is high enough to pull valence electrons from the host atoms on the p-side which are accelerated to n-side. These electrons account for high current observed at the breakdown. The emission of electrons from the host atoms due to the high electric field is known as internal field emission or field ionisation. The electric field required for field ionisation is of the order of 10^6 V/m.

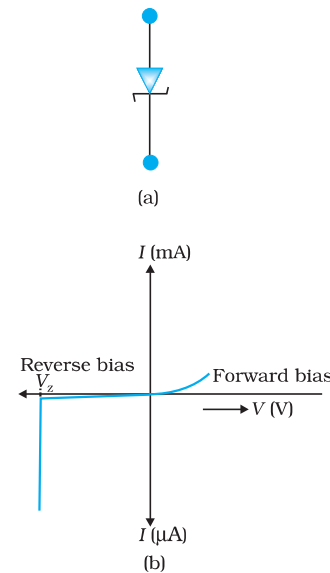


FIGURE 14.21 Zener diode, (a) symbol, (b) I-V characteristics.